



原厂直供，技术支持。 联系人：李生 电话：18126115420（微信同号）**ASC100N1200MT3**

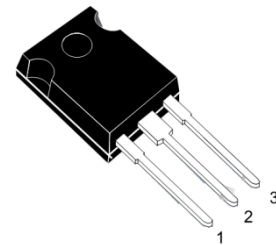
## 1200V N-Channel MOSFET

### Description

Silicon Carbide (SiC) MOSFET use a completely new technology that provide superior switching performance and higher reliability compared to Silicon. In addition, the low ON resistance and compact chip size ensure low capacitance and gate charge. Consequently, system benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size.

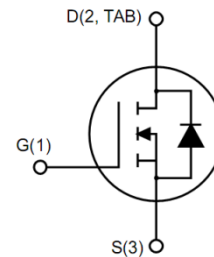
### Features

- High Speed Switching with Low Capacitances
- High Blocking Voltage with Low RDS(on)
- Simple to drive with Standard Gate Drive
- 100% avalanche tested
- Maximum junction temperature of 150°C
- ROHS Compliant



### Application

- EV Charging
- DC-AC Inverters
- High Voltage DC/DC Converters
- Switch Mode Power Supplies
- Power Factor Correction Modules
- Motor Drives



### Ordering Information

Part Number	Marking	Package	Packaging
ASC100N1200MT3	ASC100N1200MT3	TO-247	Tube



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### Absolute Maximum Ratings(Tc=25°C)

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-Source Voltage	1200	V
I <sub>D</sub>	Drain Current(continuous)at Tc=25°C	100	A
I <sub>D</sub>	Drain Current(continuous)at Tc=100°C	70	A
I <sub>DM</sub>	Drain Current (pulsed)	200	A
V <sub>GS</sub>	Gate-Source Voltage	-10/+20	V
P <sub>D</sub>	Power Dissipation T <sub>C</sub> = 25°C	425	W
T <sub>J</sub> , T <sub>stg</sub>	Junction and Storage Temperature Range	-55 to +150	°C

### Electrical Characteristics(T<sub>J</sub> = 25°C unless otherwise specified)

#### Typical Performance-Static

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV <sub>DS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> =250uA, V <sub>GS</sub> =0V	1200			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =1200V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C			100	uA
I <sub>GSS</sub>	Gate-body Leakage Current	V <sub>DS</sub> =0V ; V <sub>GS</sub> =10 to 20V			250	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> =15mA	2		4	V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> =20V, I <sub>D</sub> =50A		18	22	mΩ
R <sub>G</sub>	Gate Resistance	V <sub>GS</sub> =0V, f=1MHz		3		Ω

#### Typical Performance-Dynamic

C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =600V, f=1000KHZ, V <sub>GS</sub> =0V	4860		pF
C <sub>oss</sub>	Output Capacitance		128		pF
C <sub>rss</sub>	Reverse Transfer Capacitance		25		pF
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =600V, I <sub>D</sub> =50A, V <sub>GS</sub> =0~20V	168		nC
Q <sub>gs</sub>	Gate-source Charge		56		nC
Q <sub>gd</sub>	Gate-Drain Charge		46		nC
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>DD</sub> =600V, I <sub>D</sub> =50A, V <sub>GS</sub> =-0V~20V, R <sub>G</sub> =0Ω,	155		ns
t <sub>r</sub>	Rise Time		29		ns
t <sub>d(off)</sub>	Turn-off Delay Time		79		ns
t <sub>f</sub>	Fall Time		26		ns



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### Typical Performance-Reverse Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{FSD}$	Forward Voltage	$V_{GS}=0V, I_F=30A, T_J=25^{\circ}C$	3		6	V
		$V_{GS}=0V, I_F=30A, T_J=150^{\circ}C$	3		6	V
$t_{rr}$	Reverse Recovery Time	$V_{GS}=0V, I_F=30A,$ $V_R=600V,$ $di/dt=100A/\mu s$		86		ns
$Q_{rr}$	Reverse Recovery Charge			876		nC
$I_{rrm}$	Peak Reverse Recovery Current			20		A

### Thermal Characteristics

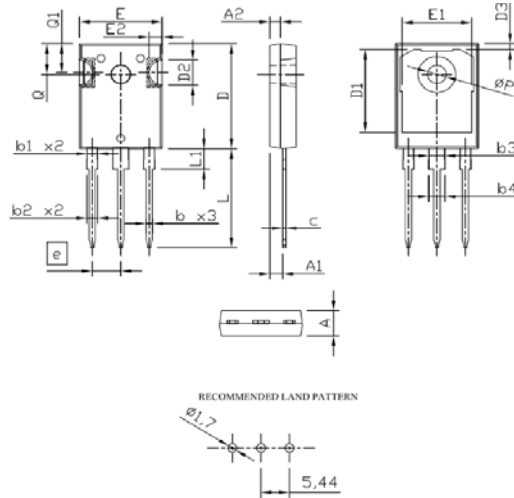
Symbol	Parameter	Value.	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.3	$^{\circ}C/W$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Air	40	$^{\circ}C/W$

The values are based on the junction-to case thermal impedance which is measured with the device mounted to a large heat sink assuming maximum junction temperature of  $T_J(max)=150^{\circ}C$



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**Package Drawing:**



**Dimensions ( UNIT: mm )**

SYMBDLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	4.90	5.00	5.10	0.193	0.197	0.201
A1	2.31	2.42	2.52	0.091	0.095	0.099
A2	1.90	2.00	2.10	0.075	0.079	0.083
b	1.16	1.22	1.27	0.046	0.048	0.050
b1	1.96	2.02	2.07	0.078	0.080	0.081
b2	2.00	2.10	2.20	0.079	0.083	0.087
b3	2.96	3.02	3.07	0.117	0.119	0.121
b4	3.00	3.10	3.20	0.118	0.122	0.126
C	0.59	0.62	0.66	0.023	0.024	0.026
D	20.90	21.00	21.10	0.823	0.827	0.831
D1	16.25	16.55	16.85	0.640	0.652	0.663
D2	5.00 TYP			0.197 TYP		
D3	1.05	1.20	1.35	0.041	0.047	0.053
e	5.44 BSC			0.214 BSC		
E	15.70	15.80	15.90	0.618	0.622	0.626
E1	13.06	13.26	13.50	0.514	0.522	0.530
E2	2.50 TYP			0.098 TYP		
L	19.72	19.92	20.12	0.776	0.784	0.792
L1	—	—	4.30	—	—	0.169
Q	6.15 BSC			0.242BSC		
Q1	5.60	5.80	6.00	0.220	0.228	0.236
ØP	3.55	3.60	3.70	0.140	0.142	0.146